

first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1 \times 10^{17}/\text{cm}^3$ so that said second nitride semiconductor layer of good crystallinity is grown,

wherein said second nitride semiconductor layer is a thick layer of which impurity concentration and a thickness are set so as to decrease resistivity thereof,

wherein said third nitride semiconductor layer is a thin layer of which impurity concentration is set within $1 \times 10^{17}/\text{cm}^3$ so that a crystallinity is better than that of second nitride semiconductor layer and of which thickness is set so as to decrease the V_f by preventing a resistivity from increasing.

32. (new) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein an impurity concentration of said first nitride semiconductor layer and an impurity concentration of said third nitride semiconductor layer are lower than that of said second nitride semiconductor layer,

wherein said second nitride semiconductor layer is a thick layer and said third nitride semiconductor layer is a thin layer.

33. (new) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1 \times 10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1 \times 10^{17}/\text{cm}^3$,

wherein said second nitride semiconductor layer is a thick layer of which thickness is set $1\mu\text{m}$ or more and said third nitride semiconductor layer is a thin layer.

34. (new) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride

semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein an impurity concentration of said first nitride semiconductor layer is set within $1 \times 10^{17}/\text{cm}^3$ and an impurity concentration of said third nitride semiconductor layer is set within $1 \times 10^{17}/\text{cm}^3$,

wherein said second nitride semiconductor layer is a thick layer of which thickness is set $1\mu\text{m}$ or more and of which impurity concentration is set higher than that of said first and third nitride semiconductor layers,

wherein said third nitride semiconductor layer is a thin layer of which thickness is set not exceeding $0.5\mu\text{m}$.

35. (new) A nitride semiconductor light emitting device comprising; a substrate, an active layer, a p-type contact layer and a three layer laminated structure sandwiched by said substrate and said active layer, said three layer laminated structure having a first nitride semiconductor layer, a second nitride semiconductor layer and a third nitride semiconductor layer, said second nitride semiconductor layer positioned between said first nitride semiconductor layer and said third nitride semiconductor layer, said third nitride semiconductor layer positioned between said second nitride semiconductor layer and said active layer,

wherein an impurity concentration of said first nitride semiconductor layer and an impurity concentration of said third nitride semiconductor layer are set lower than that of said second nitride semiconductor layer,

wherein said second nitride semiconductor layer is a thick layer of which thickness is set $1\mu\text{m}$ or more,

wherein said third nitride semiconductor layer is a thin layer of which thickness is set not exceeding $0.5\mu\text{m}$.

36. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, further comprising a buffer layer of nitride semiconductor between said substrate and said first nitride semiconductor layer.

37. (new) The nitride semiconductor light emitting device according to claim 36, wherein a thickness of said first nitride semiconductor layer is thicker than said buffer layer.

38. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, further comprising an n-type cladding layer of nitride semiconductor between said third nitride semiconductor layer and said active layer.

39. (new) The nitride semiconductor light emitting device as in claim 31 or 32, wherein a thickness of said second nitride semiconductor layer is set $0.1\mu\text{m}$ or more and a thickness of said third nitride semiconductor layer is set not exceeding $0.1\mu\text{m}$.

40. (new) The nitride semiconductor light emitting device according to claim 39, wherein said first nitride semiconductor layer is undoped GaN or AlGaN, said second

nitride semiconductor layer is Si-doped GaN and said third nitride semiconductor layer is one of undoped GaN, AlGa~~N~~ and InGa~~N~~.

subcl 41. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, wherein said third nitride semiconductor layer is made of InGa~~N~~.

42. (new) The nitride semiconductor light emitting device according to claim 41, further comprising a nitride semiconductor layer having Al between said third semiconductor layer and said active layer.

subcl 43. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, wherein said first to third nitride semiconductor layers have a same composition.

44. (new) The nitride semiconductor light emitting device according to claim 43, wherein said first to third nitride semiconductor layers are made of Ga~~N~~.

45. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, wherein said second nitride semiconductor layer is in contact with said first nitride semiconductor layer and said third nitride semiconductor layer.

subcl 46. (new) The nitride semiconductor light emitting device as in claim 31, 32, 33, 34 or 35, wherein said second nitride semiconductor layer is a super lattice layer made by laminating the low doped nitride semiconductor layers of n-type impurity and the high doped nitride semiconductor layers of n-type impurity.

47. (new) The nitride semiconductor light emitting device according to claim 46, wherein said second nitride semiconductor layer is a super lattice layer of combination of

nitride layers selected from the group consisting of GaN/GaN, InGaN/GaN, AlGaIn/GaN
and InGaIn/AlGaIn.-